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(54) **Title**: A METHOD FOR FORMING A SELECTIVE CONTACT

(57) **Abstract**: The present invention is directed to a method for forming a selective contact for a photovoltaic cell comprising: a. forming a doped contact layer at the surface of a semiconductor substrate; b. annealing a portion of the doped contact layer with a laser beam, said portion having a 2D-pattern corresponding to at least a portion of a respective selective contact grid; characterized in that the laser beam is pulsed and shaped to the 2D-pattern. In addition, the present invention is also directed to a photovoltaic cell comprising a selective contact formed by that method.